

AMENDMENTS TO THE CLAIMS

Kindly amend claims **1, 8, 9, 11** and **13**, cancel claim **14**, and add new claims **26-34** as shown in the listing of claims below. This listing of claims will replace all prior versions, and listings of claims in the application.

LISTING OF CLAIMS

- 1 Claim 1. (currently amended) A method for a controlled release of structures comprising:
2 a) forming one or more trenches in a layer of device material;
3 b) filling one or more selected trenches with an etch-stop material to form one or more
4 etch-stop trenches;
5 c) defining one or more structures between the selected trenches;
6 d) forming a structural layer proximate one or more exposed areas of the device layer,
7 wherein the structural layer includes one or more structures that are formed directly
8 on top of an etch-stop layer; and
9 e) etching one or more portions of the device layer between the etch-stop trenches to
10 release the structures, wherein the etching does not etch the etch-stop material.
- 1 Claim 2. (original) The method of claim 1, wherein b) includes depositing etch-stop material
2 over the surface of the device layer.
- 1 Claim 3. (original) The method of claim 2 wherein c) includes forming one or more openings
2 in the etch-stop material that has been deposited over the surface of the device layer.
- 1 Claim 4. (original) The method of claim 2, wherein the etching undercuts one or more portions
2 of the etch-stop material that has been deposited over the surface of the device layer.
- 1 Claim 5. (original) The method of claim 1 where the layer of device material is disposed
2 between two layers of etch-stop material.
- 1 Claim 6. (original) The method of claim 1, wherein the device layer includes one or more
2 layers of a silicon-on-insulator (SOI) substrate.
- 1 Claim 7. (original) The method of claim 1, wherein the device layer is a layer of glass, quartz
2 or oxide.

1 Claim 8. (currently amended) The method of claim 1, wherein [[d]] e includes a wet etch
2 process.

1 Claim 9. (currently amended) The method of claim 1, wherein [[d]] e includes a dry etch
2 process.

1 Claim 10. (cancel)

1 Claim 11. (currently amended) The method of claim 1, wherein the etch process in [[d]] e does
2 not etch the structural layer.

1 Claim 12. (previously presented) The method of claim 1, further comprising releasing one or
2 more portions of the structural layer.

1 Claim 13. (currently amended) The method of claim 1, wherein the etch process in [[d]] e
2 releases one or more portions of the structural layer.

1 Claim 14. (cancel)

1 Claim 15. (original) The method of claim 14, wherein the structural layer contains two or more
2 sub-layers.

1 Claim 16. (previously presented) A process for forming structures comprising:

- 2 i) forming one or more trenches in a layer of device material;
- 3 ii) filling one or more selected trenches with an etch-stop material to form one or more etch-
4 stop trenches;
- 5 iii) masking a surface of the layer of device material to expose one or more selected areas of
6 device material that border one or more of the etch-stop trenches; and
- 7 iv) forming one or more structures on one or more of the selected areas of the device
8 material that were exposed; and
- 9 v) etching one or more of the selected areas of the device layer to release the structures,
10 wherein the etching does not etch the etch-stop material.

1 Claims 17-22 (cancel)

1 Claim 23. (previously presented) The method of claim 1, wherein the structural layer is
2 protected by one or more etch-stop layers.

1 Claim 24. (previously presented) The method of claim 16, wherein one or more of the structures
2 include a device layer protected by one or more etch-stop layers.

1 Claim 25. (cancel)

1 Claim 26. (new) The method of claim 16, wherein filling one or more selected trenches with an
2 etch-stop material includes depositing etch-stop material over the surface of the device layer.

1 Claim 27. (new) The method of claim 26 wherein masking a surface of the layer of device
2 material includes forming one or more openings in the etch-stop material that has been
3 deposited over the surface of the device layer.

1 Claim 28. (new) The method of claim 26, wherein the etching one or more of the selected areas
2 of the device layer undercuts one or more portions of the etch-stop material that has been
3 deposited over the surface of the device layer.

1 Claim 29. (new) The method of claim 16 where the layer of device material is disposed between
2 two layers of etch-stop material.

1 Claim 30. (new) The method of claim 16, wherein the device material includes one or more
2 layers of a silicon-on-insulator (SOI) substrate.

1 Claim 31. (new) The method of claim 16, wherein the device material includes glass, quartz or
2 oxide.

1 Claim 32. (new) The method of claim 16, wherein etching one or more of the selected areas of
2 the device layer includes a dry etch or wet etch process.

1 Claim 33. (new) The method of claim 16, wherein etching one or more of the selected areas of
2 the device layer does not etch the structures.

1 Claim 34. (new) The method of claim 33, wherein the structures include two or more sub-
2 layers.